

Hybrid Dielectric Materials for Device Technologies: *Understanding Relationships between Molecular Structure and Properties*

Karsu I. Kilic and Reinhold H. Dauskardt
Materials Science and Engineering
Stanford University

8 Industry Liaisons, including:
INTEL, IBM, TSMC, Samsung

This work was supported by Semiconductor Research Corporation (SRC) Program under task ID 2957.001.

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Low-Dielectric Constant Hybrid Organosilicate Glasses

microelectronics

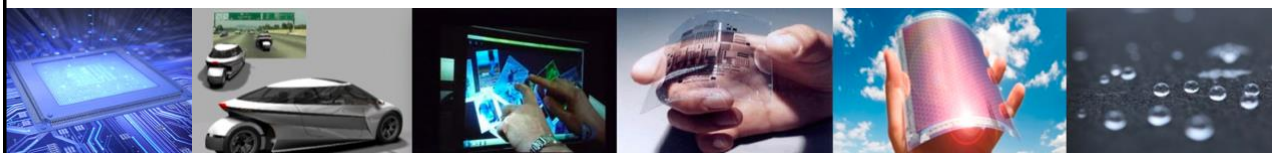
light weighting

display

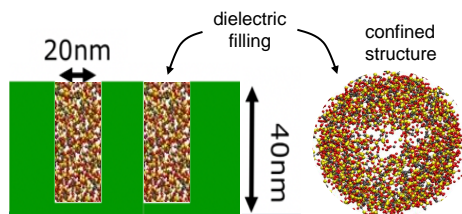
flexible

solar

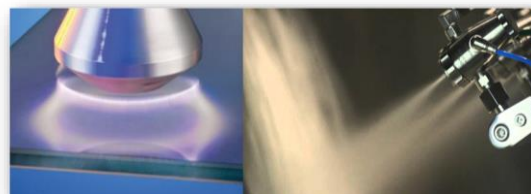
protective



*Nanoscale Confinement of Low-k Dielectric
in Interconnect Devices*



Application to other areas involving
open-air spray-plasma deposition



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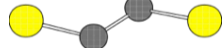
Molecular Modeling of Hybrid Dielectric Materials

Simulation Elements

Oxygen:



OCS:



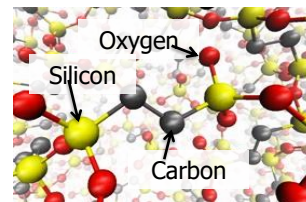
H atoms are modeled implicitly (united atom approach)

Bonded Interactions

$$U(r) = k(r - r_0)^2 \quad (\text{parameterized using ab-initio methods})$$

$$U(r) = k(\theta - \theta_0)^2$$

$$U(\phi) = \frac{1}{2}K_1[1 + \cos \phi] + \frac{1}{2}K_2[1 - \cos 2\phi] + \frac{1}{2}K_3[1 + \cos 3\phi] + \frac{1}{2}K_4[1 - \cos 4\phi]$$



Non-Bonded Interactions

Stillinger-Weber Potential

$$U = \sum_i \sum_{j>i} \phi_2(r_{ij}) + \sum_i \sum_{j \neq i} \sum_{k>j} \phi_3(r_{ij}, r_{ik}, \theta_{ijk})$$

$$\phi_2(r) = A\epsilon \left[B \left(\frac{\sigma}{r} \right)^p - \left(\frac{\sigma}{r} \right)^q \right] \exp \left(\frac{\sigma}{r - a\sigma} \right)$$

$$\phi_3(r, s, \theta) = \lambda\epsilon [\cos \theta - \cos \theta_0]^2 \exp \left(\frac{\gamma\sigma}{r - a\sigma} \right) \exp \left(\frac{\gamma\sigma}{s - a\sigma} \right)$$

Reactive Force Potentials

$$E_{\text{system}} = E_{\text{bond}} + E_{\text{over}} + E_{\text{under}} + E_{\text{lp}} + E_{\text{val}} + E_{\text{pen}} + E_{\text{tors}} + E_{\text{conj}} + E_{\text{vdWaaals}} + E_{\text{Coulomb}}$$

(With the inclusion of H atoms)

Ters-off Potential

$$E = \sum_i E_i = \frac{1}{2} \sum_{i \neq j} V_{ij}$$

$$V_{ij} = f_c(r_{ij}) [f_R(r_{ij}) + b_{ij} f_A(r_{ij})]$$

$$f_R(r_{ij}) = A_{ij} \exp(-\lambda_{ij} r_{ij})$$

$$f_A(r_{ij}) = B_{ij} \exp(-\mu_{ij} r_{ij})$$

$$f_c(r_{ij}) = \begin{cases} 1, & r_{ij} < R_{ij} \\ \frac{1}{2} + \frac{1}{2} \cos \left(\pi \frac{r_{ij} - R_{ij}}{S_{ij} - R_{ij}} \right), & R_{ij} < r_{ij} < S_{ij} \\ 0, & r_{ij} > S_{ij} \end{cases}$$

$$b_{ij} = \chi_{ij} (1 + \beta_i^{n_i} \zeta_i^{n_i})^{-1/2n_i}$$

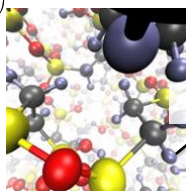
$$\zeta_{ij} = \sum_{k \neq i, j} f_c(r_{ik}) \omega_{ik} g(\theta_{ijk})$$

$$g(\theta_{ijk}) = 1 + \frac{c_i^2}{d_i^2} - c_i^2 / [d_i^2 + (h_i - \cos \theta_{ijk})^2]$$

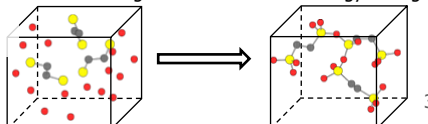
$$\lambda_{ij} = (\lambda_i + \lambda_j)/2, \quad \mu_{ij} = (\mu_i + \mu_j)/2$$

$$A_{ij} = (A_i + A_j)/2, \quad B_{ij} = (B_i + B_j)/2$$

$$R_{ij} = (R_i R_j)^{1/2}, \quad S_{ij} = (S_i S_j)^{1/2}$$



Initial Random Configuration Final Low Energy Configuration



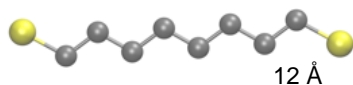
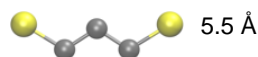
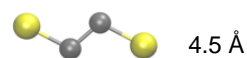
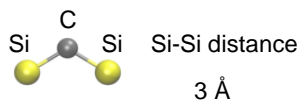
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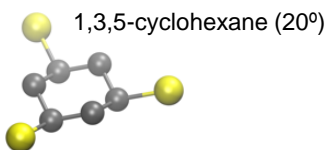
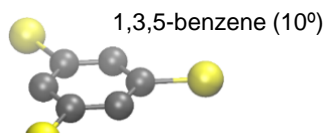
Precursors with Different Molecular Geometry and Connectivity

All modeled with Hartree-Fock Ab-initio simulations for molecular structure and optimized bonded potentials.

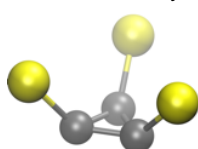
precursor chain length



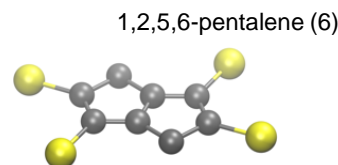
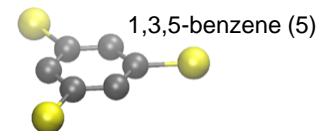
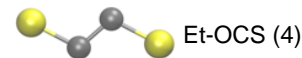
precursor planarity



1,2,3-cyclopropane (50°)



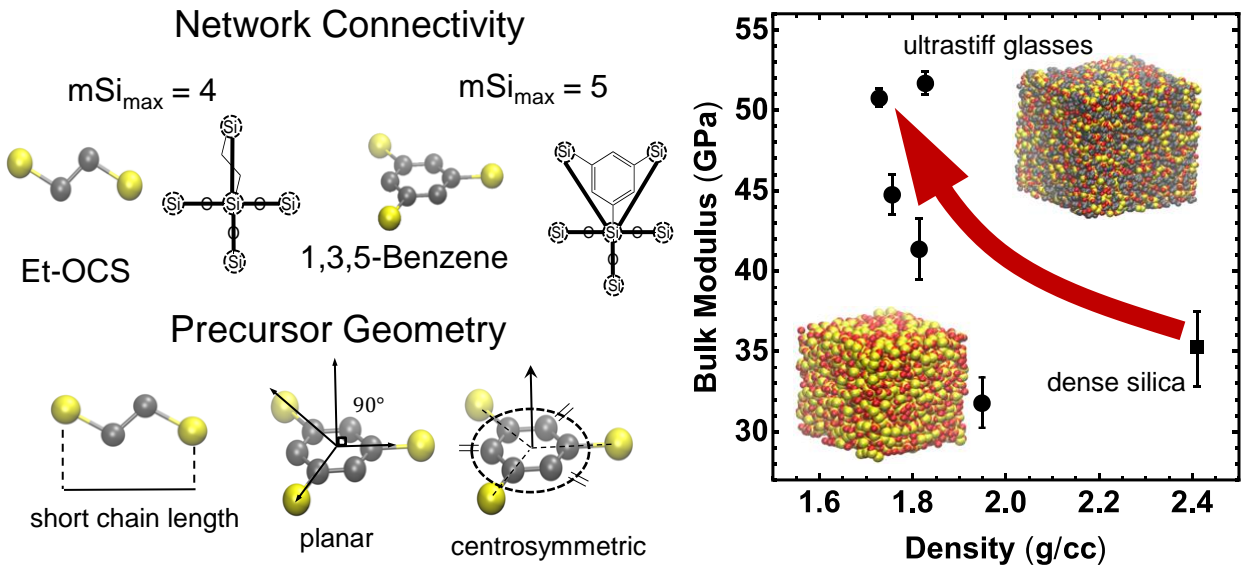
precursor connectivity (mSi)



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Design of Ultrastiff Low-k Hybrid Organosilicate Glasses

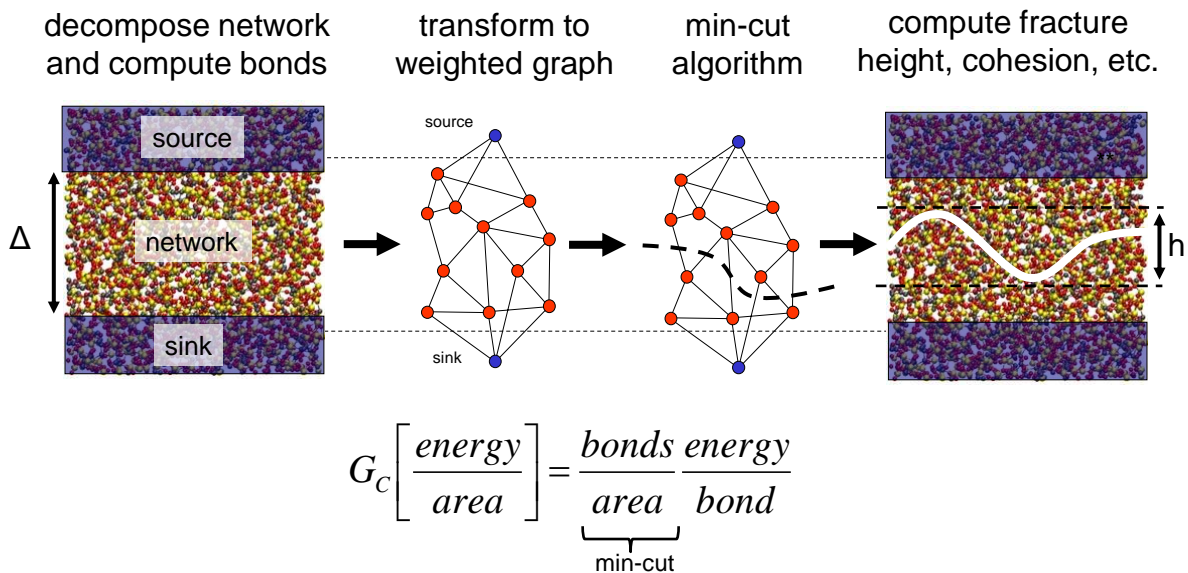


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K.I. Kilic & R.H. Dauskardt, *Advanced Functional Materials*, 2019.

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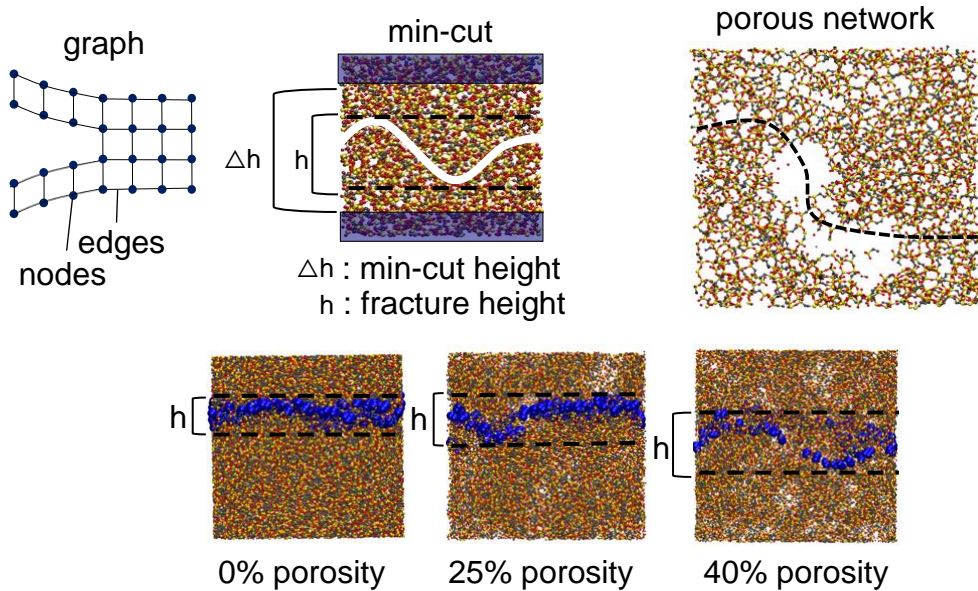
Simulating the Fracture Properties with Graph Theory



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Simulating the Fracture Properties with Graph Theory

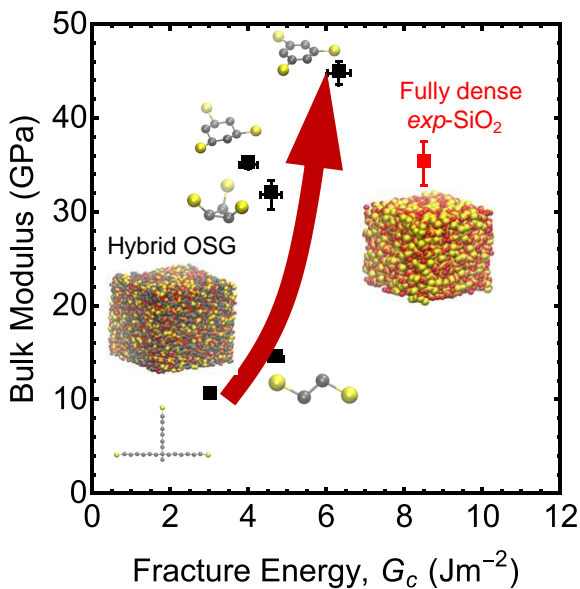


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Kilic et al., Mechanically reliable hybrid organosilicate glasses for advanced interconnects, Journal of Vacuum Science & Technology B, (2020).

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Hyperconnected Planar Precursors Enhance Elastic and Fracture Properties

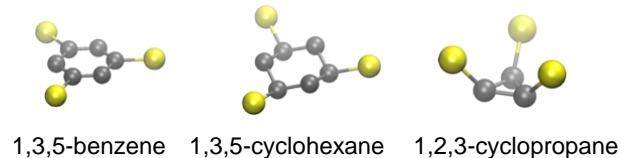


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Kilic et al., Mechanically reliable hybrid organosilicate glasses for advanced interconnects, Journal of Vacuum Science & Technology B, (2020).

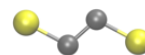
Cyclic Organic Chains

Hyperconnected ($m\text{Si}_{\text{max}} = 5$)

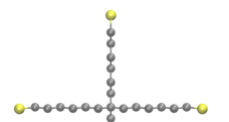


Acyclic Organic Chains

Conventionally connected
($m\text{Si}_{\text{max}} = 4$)



Hyperconnected
($m\text{Si}_{\text{max}} = 5$)

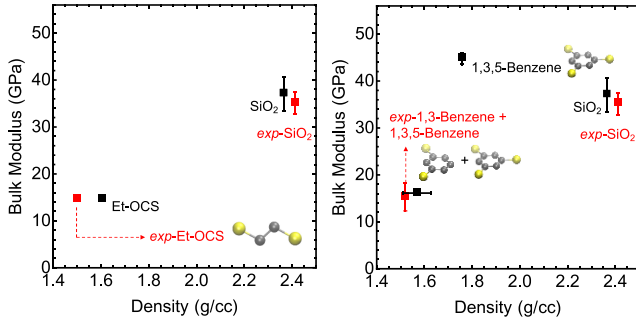


R = CH₂

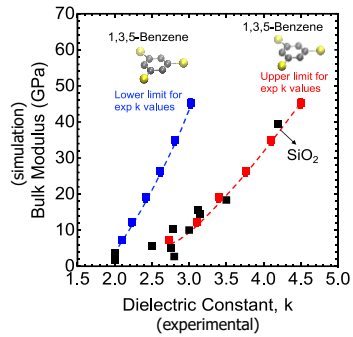
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Experimental Results for the low-k Hybrid OSG Networks

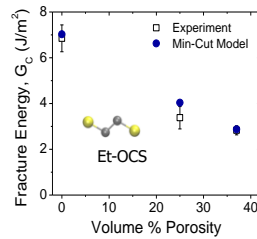
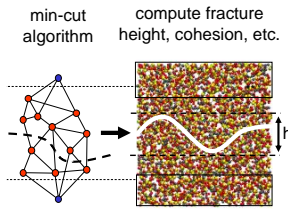
Elastic Properties



Dielectric Properties

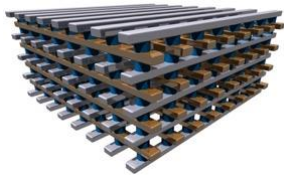


Fracture Properties



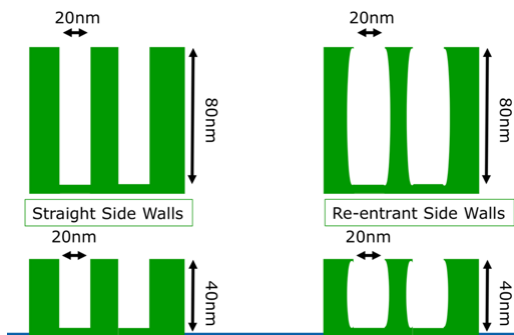
Rasadujjaman et al., Analytical Study of Porous Organosilicate Glass Films Prepared from Mixtures of 1,3,5- and 1,3-Alkoxyisilybenzenes, *Materials*, 2021.
 Liu et al., Properties of organosilicate low-k films with 1,3- and 1,3,5-benzene bridges between Si atoms, *Japanese Journal of Applied Physics*, 2020.
 Burg et al., Hyperconnected molecular glass network architectures with exceptional elastic properties, *Nature Comm.* (2017)

Effects of Nanoscale Device Confinement

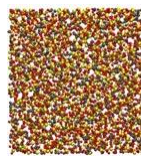


Predicting the role of nano-scale geometrical confinement on the structure and mechanical reliability of hybrid organosilicate materials

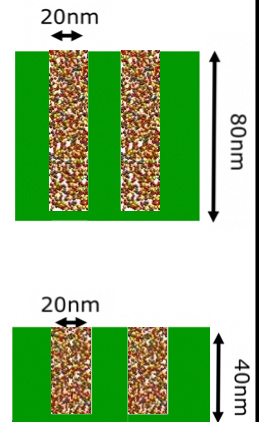
Relevant Trench Geometries



Low-k dielectric hybrid organosilicate network

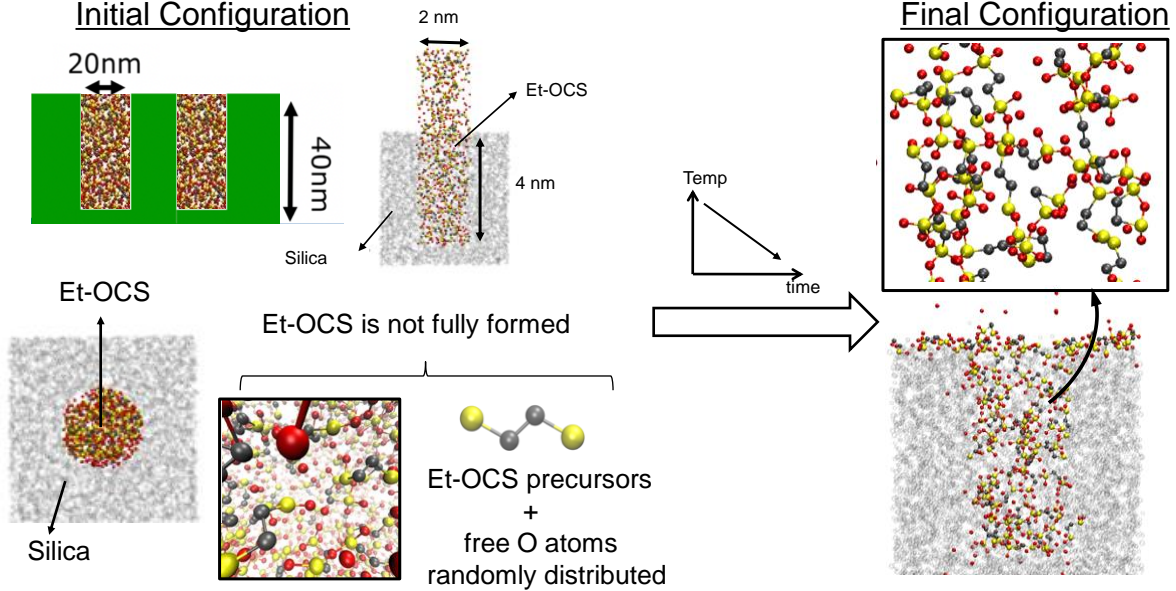


Filled into the patterned device structure



Methodology to Simulate Nanoconfinement Effects

Initial Configuration

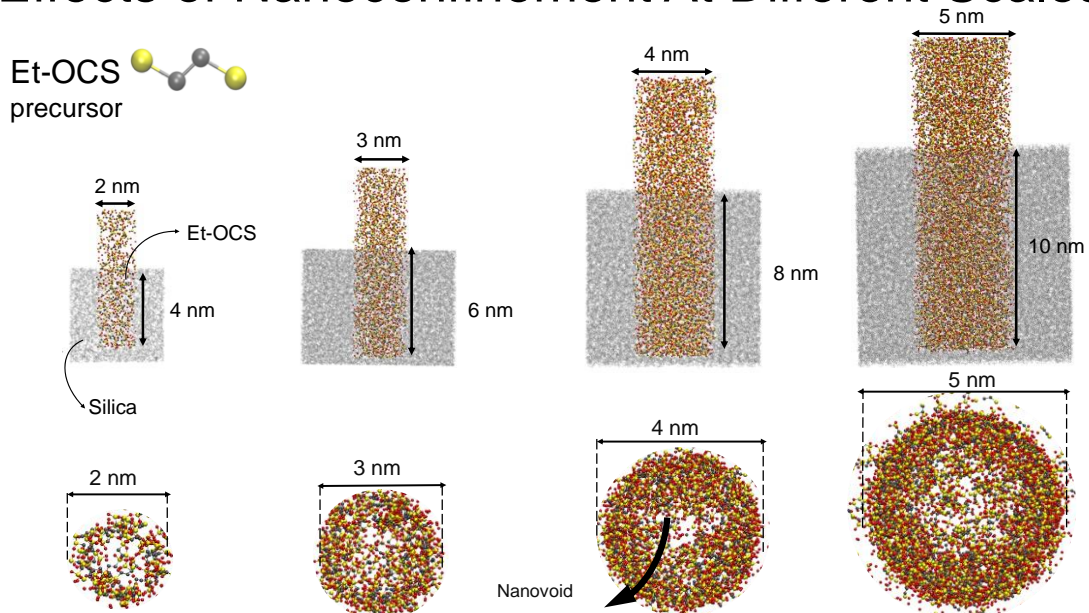


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Kilic et al., Computational Analysis of the Role of Nanoconfinement on the Reliability of ULK Glasses, *Proceedings of IEEE (IITC)*, 2022.

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Effects of Nanoconfinement At Different Scales



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Kilic et al., Computational Analysis of the Role of Nanoconfinement on the Reliability of ULK Glasses, *Proceedings of IEEE (IITC)*, 2022.

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Experimental Validation for Nanoconfinement Effects: Literature

Experimental Results

Void formation

Lee et al., Novel Flowable CVD Process Technology for sub-20nm Interlayer Dielectrics, IEEE.

Simulation Results

Silica (trench)

OSG filling

Et-OCS

Shrinkage

Gap

Void

after crosslinking

Kobayashi et al., Plasma-Enhanced CVD Low-k Process Enabling Global Planarity by Controlling Flowability, IEEE, 2014

“There is a need to provide alternative precursor compounds to produce silicon - containing films via flow CVD techniques...”

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Ahner et al., Thermal stability and gap-fill properties of spin-on MSQ low-k dielectrics, Microelectronic Engineering, 2007

Sun et al., STI Gap Fill Technology and Flowable CVD Process Application, IEEE.

Deng et al., New Applications and Challenges of Dielectric Films at 14 nm FinFet Technology and Beyond, IEEE.

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Analyzing Trench-Filling Sidewall Interactions

Strong Si-O interactions
Si-O bonding on the interface

Weak Si-O interactions
No bonding on the interface

Atoms on the inner trench walls

Trench – filling interaction gets weaker

Dimensions: 4 nm x 8 nm
4 nm

Dimensions: 4 nm x 8 nm
4 nm

Dimensions: 4 nm x 8 nm
4 nm

More material loss inside the gap!

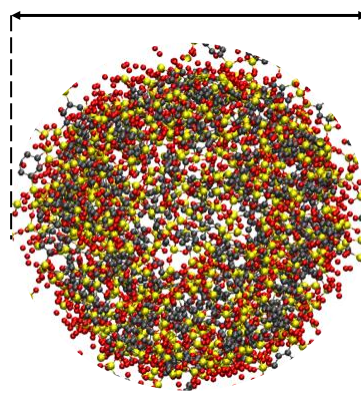
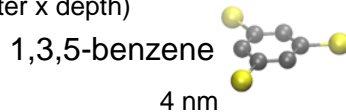
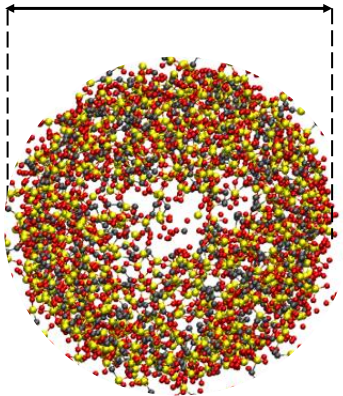
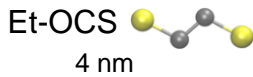
OSG filling molecules accumulate towards the center when trench-filling interaction is weak, however less material remains inside the gap. Attractive interactions between trench and filling helps keep more material inside the gap despite the central void formation.

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The Role of Organosilicate Precursors

Gap dimensions: 4 nm x 8 nm (diameter x depth)



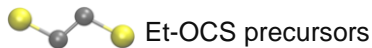
Suggested strategy to minimize nanovoid size: Use of precursors that interact effectively with one another to crosslink under confinement, such as the 1,3,5-benzene precursors

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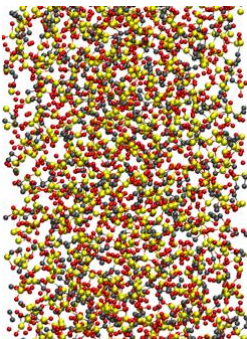
Kilic et al., Computational Analysis of the Role of Nanoconfinement on the Reliability of ULK Glasses, *Proceedings of IEEE (IITC)*, 2022.

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Effects of Nanoconfinement on Elastic Properties

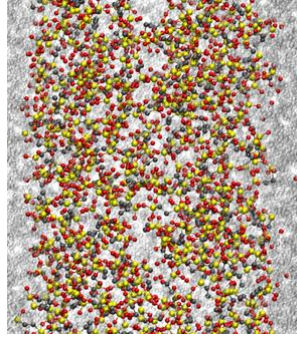


No confinement

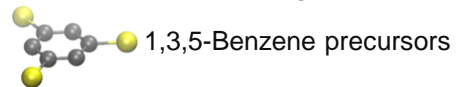


mSi = 3.4
Density = 1.6 g/cc
Young's Modulus ~ 21 GPa

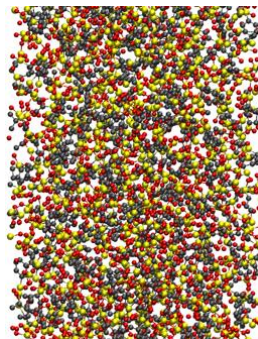
Under confinement



mSi = 2.88
Density = 1.05 g/cc
Young's Modulus ~ 2.5 GPa

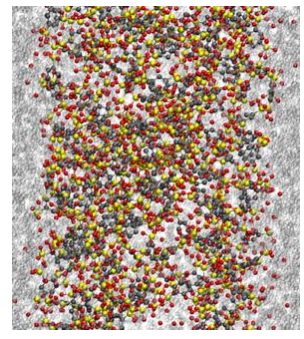


No confinement



mSi = 4.4
Density = 1.8 g/cc
Young's Modulus ~ 61 GPa

Under confinement



mSi = 3.62
Density = 1.13g/cc
Young's Modulus ~ 7.2 GPa

1,3,5-benzene precursors form a stiffer network with better mechanical properties under nanoconfinement!

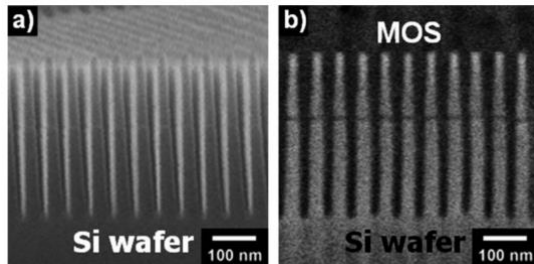
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Kilic et al., Computational Analysis of the Role of Nanoconfinement on the Reliability of ULK Glasses, *Proceedings of IEEE (IITC)*, 2022.

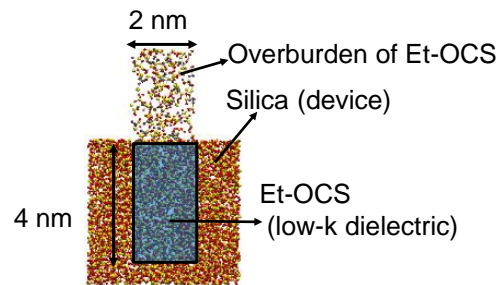
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Papers with Similar Experimental Results and Trends...

Device features: 25 nm width, 400 nm depth
 Inner device walls are covered with silica
 Filling material is mesoporous OSG



Device features: 2 nm width, 4 nm depth



Final configuration has 53-56% porosity
 Young's Modulus drops from
 9 GPa to ~6 GPa

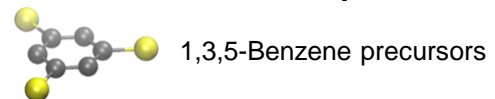
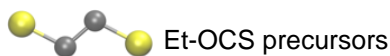
Our predictions for Young's Modulus are:
 ~ 2.5 GPa for Et-OCS and
 ~ 7.2 GPa for 1,3,5-Benzene

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Jang et al., Fabrication of mesoporous organosilica in a shallow nanotrench for low-k and high elastic modulus material application, *Journal of Materials Chemistry*, 2012.

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Effects of Nanoconfinement on Fracture Properties

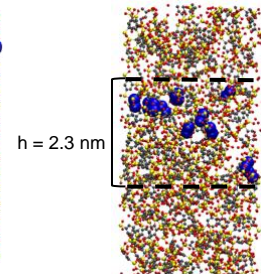
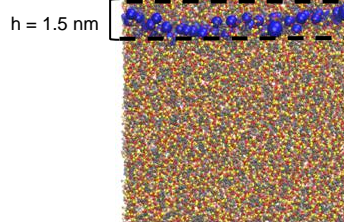
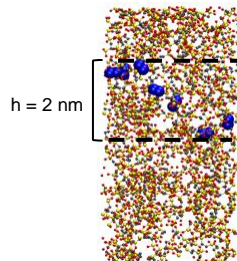
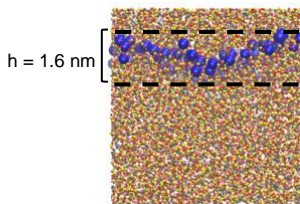


No confinement

Under confinement

No confinement

Under confinement



mSi = 3.4
 Fracture bond density
 1.9 nm^{-2}

mSi = 2.88
 Fracture bond density
 0.24 nm^{-2}

mSi = 4.4
 Fracture bond density
 2.5 nm^{-2}

mSi = 3.62
 Fracture bond density
 0.35 nm^{-2}

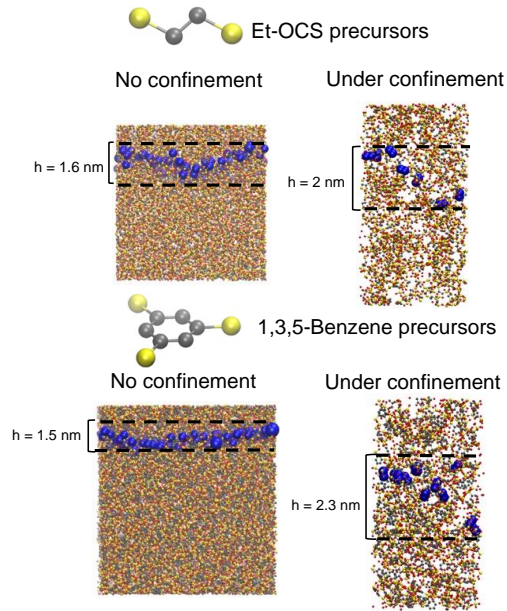
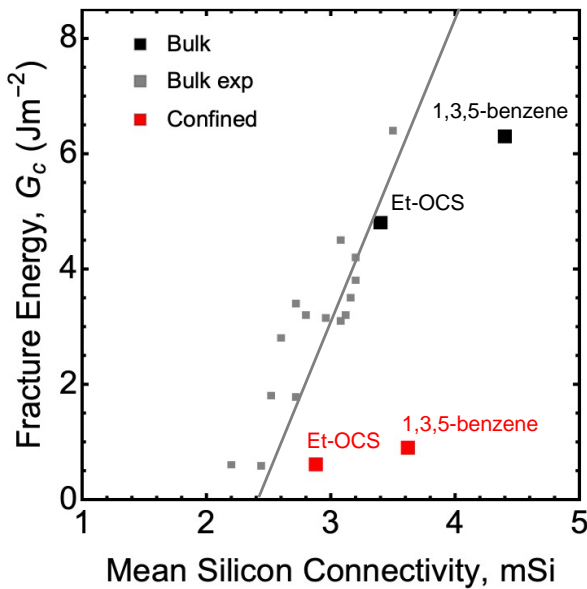
1,3,5-benzene network has better fracture properties under confinement!

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Kilic et al., Computational Analysis of the Role of Nanoconfinement on the Reliability of ULK Glasses, *Proceedings of IEEE (IITC)*, 2022.

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Effects of Nanoconfinement on Fracture Properties

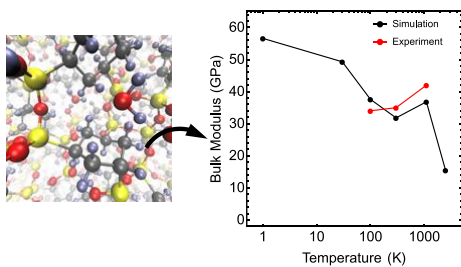


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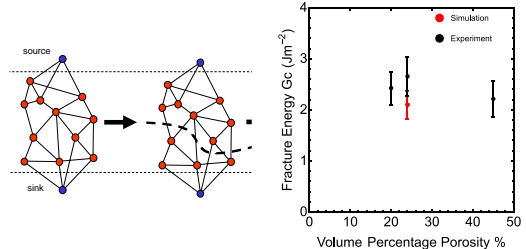
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ReaxFF for Effects of Moisture and Extreme Temperature

ReaxFF simulations capture the anomalous increase in silica stiffness with temperature

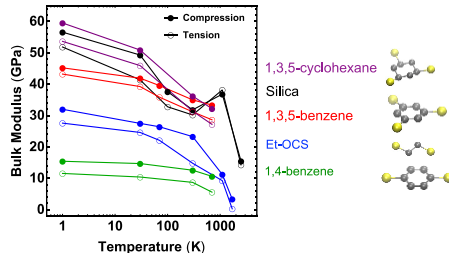


Fracture energies of nanoporous SiCH_3 networks in presence of moisture

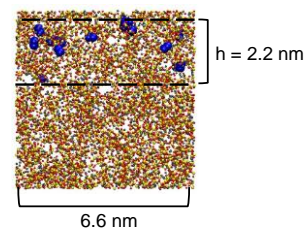


ReaxFF simulations show temperature dependant stiffness of OSG dielectrics

Absence of anomalous behavior seen in silica



Min-cut algorithm for fracture path prediction including moisture effects



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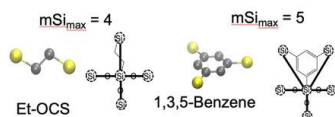
20

Predicting Structure-Property Relationships with ML

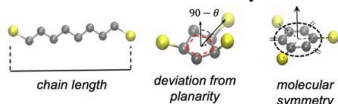
Features (inputs)

Molecular features

Network Connectivity

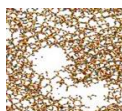


Precursor Geometry



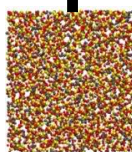
Macroscopic features

Porosity, condensation degree q , precursor fragmentation

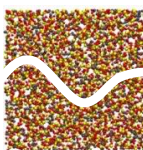


Outputs

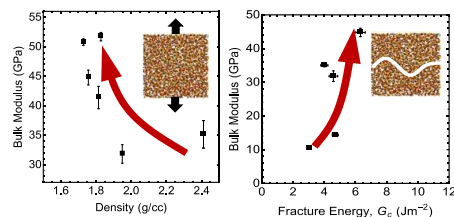
Elastic Modulus, E
"stiffness"



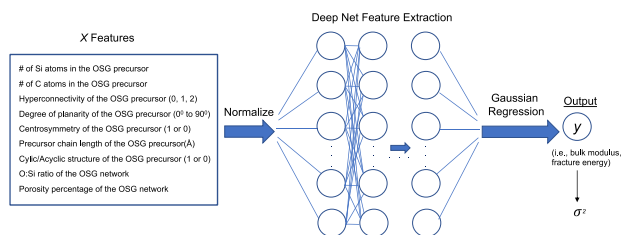
Fracture Energy, G_c
"toughness"



Design of Reliable low-k hybrids



Machine Learning

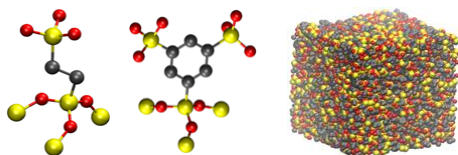


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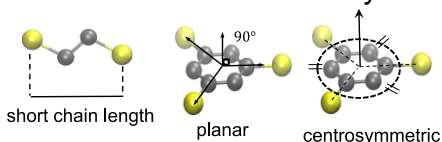
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Conclusion

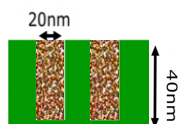
Molecular structure



Precursor Geometry



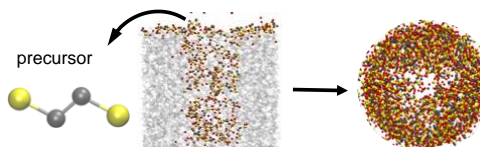
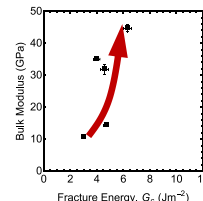
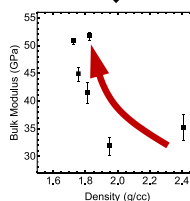
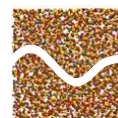
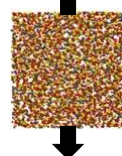
Nanoscale Confinement



Mechanical properties

Elastic

Fracture



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